

Dual N-channel 40 V, 8.5 m $\Omega$  standard level MOSFET

6 November 2013

Product data sheet

### 1. General description

Dual standard level N-channel MOSFET in an LFPAK56D (Dual Power-SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

### 2. Features and benefits

- Dual MOSFET
- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with  $V_{GS(th)}$  of greater than 1 V at 175  $^\circ\text{C}$

### 3. Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

### 4. Quick reference data

Table 1. Qu	lick reference data						
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	40	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; Tmb = 25 °C; <u>Fig. 1</u>	[1]	-	-	30	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	-	53	W
Static charac	teristics FET1 and FET2						
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C; Fig. 11		-	7	8.5	mΩ
Dynamic cha	racteristics FET1 and FE	T2					
Q <sub>GD</sub>	gate-drain charge	$I_D = 15 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 10 \text{ V};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 13}}; \underline{\text{Fig. 14}}$		-	7.8	-	nC

[1] Continuous current is limited by package.

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# 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source1		D1 D1 D2 D2
2	G1	gate1		
3	S2	source2		
4	G2	gate2	$\bigcirc$	
5	D2	drain2		 S1 G1 S2 G2
6	D2	drain2		mbk725
7	D1	drain1	1 2 3 4 LFPAK56D (SOT1205)	
8	D1	drain1		

# 6. Ordering information

Table 3. Ordering in	formation						
Type number	Package	Ige					
	Name	Description	Version				
BUK7K8R7-40E	LFPAK56D	Plastic single ended surface mounted package (LFPAK56D); 8 leads	SOT1205				

### 7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK7K8R7-40E	78E740

# 8. Limiting values

#### Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	40	V
V <sub>DGR</sub>	drain-gate voltage	R <sub>GS</sub> = 20 kΩ		-	40	V
V <sub>GS</sub>	gate-source voltage	T <sub>j</sub> ≤ 175 °C; DC		-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; Tmb = 25 °C; <u>Fig. 1</u>	[1]	-	30	А
		T <sub>mb</sub> = 100 °C; V <sub>GS</sub> = 10 V; <u>Fig. 1</u>	[1]	-	30	А
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; pulsed; $t_p \le 10 \ \mu$ s; Fig. 4		-	225	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	53	W
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# **BUK7K8R7-40E**

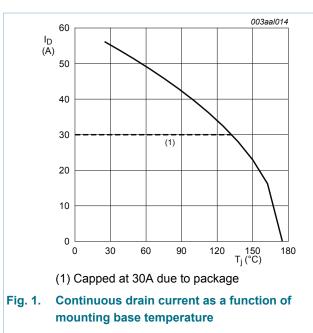
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Symbol	Parameter	Conditions		Min	Max	Unit	
T <sub>stg</sub>	storage temperature			-55	175	°C	
Tj	junction temperature			-55	175	°C	
Source-drain diode FET1 and FET2							
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[1]	-	30	А	
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^\circ C$		-	225	А	
Avalanche Ruggedness FET1 and FET2							
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$\begin{split} I_D &= 30 \text{ A};  \text{V}_{sup} \leq 40  \text{V};  \text{V}_{GS} = 10  \text{V}; \\ \text{T}_{j(\text{init})} &= 25 ^{\circ}\text{C};  \underline{\text{Fig. } 3} \end{split}$	[2][3]	-	84	mJ	

[1] Continuous current is limited by package.

[2] Refer to application note AN10273 for further information

[3] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C



 $V_{GS} \ge 10V$ 

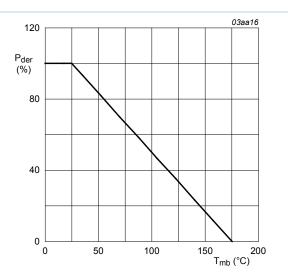
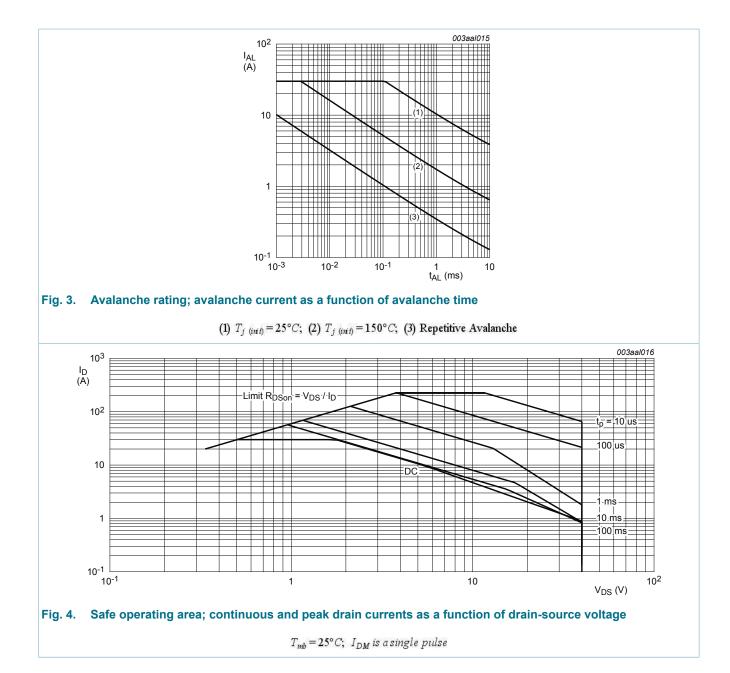


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

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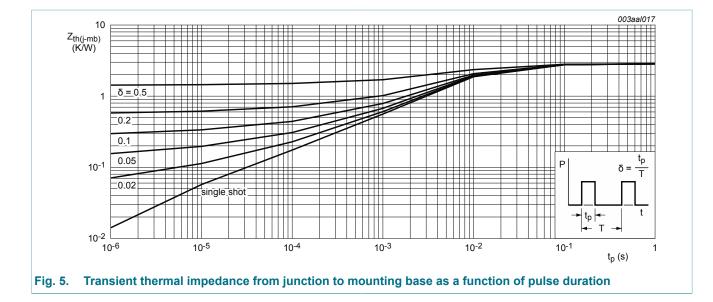


### 9. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	-	2.84	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	95	-	K/W

#### Table 6. Thermal characteristics

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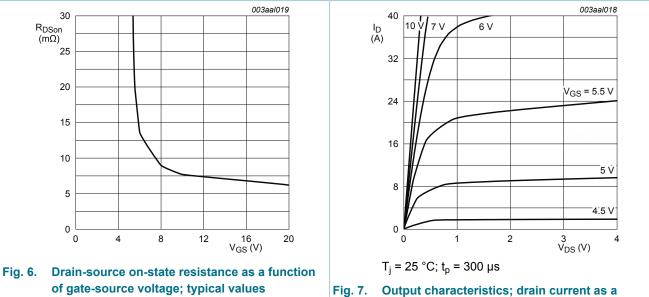
# **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
Static chara	acteristics FET1 and FET2						
V <sub>(BR)DSS</sub>	drain-source	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = -55 °C	36	-	-	V	
	breakdown voltage	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	40	-	-	V	
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 9; Fig. 10	2.4	3	4	V	
		$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 175 °C; Fig. 9; Fig. 10	1	-	-	V	
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 9; Fig. 10	-	-	4.5	V	
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = 40 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	0.02	1	μA	
		$V_{DS}$ = 40 V; $V_{GS}$ = 0 V; $T_j$ = 175 °C	-	-	500	μA	
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA	
		$V_{GS}$ = 20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA	
R <sub>DSon</sub> drain-source or resistance	R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C; Fig. 11	-	7	8.5	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 175 °C; Fig. 11; Fig. 12	-	13.8	16.7	mΩ	
Dynamic ch	naracteristics FET1 and FE	T2	I.				
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 15 A; V <sub>DS</sub> = 32 V; V <sub>GS</sub> = 10 V;	-	21.8	-	nC	
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C; <u>Fig. 13; Fig. 14</u>	-	5.9	-	nC	
Q <sub>GD</sub>	gate-drain charge	1	-	7.8	-	nC	

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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
C <sub>iss</sub>	input capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 25 V; f = 1 MHz; T <sub>i</sub> = 25 °C; Fig. 15	-	1079	1439	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 15</u>	-	235	282	pF
C <sub>rss</sub>	reverse transfer capacitance		-	149	204	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 32 V; $R_L$ = 2.4 $\Omega$ ; $V_{GS}$ = 10 V; $R_{G(ext)}$ = 5 $\Omega$ ; $T_j$ = 25 °C; $I_D$ = 15 A	-	7.4	-	ns
t <sub>r</sub>	rise time		-	12	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	13.8	-	ns
t <sub>f</sub>	fall time		-	10.3	-	ns
Source-dra	in diode FET1 and FET2		1			
V <sub>SD</sub>	source-drain voltage	$I_{S}$ = 15 A; $V_{GS}$ = 0 V; $T_{j}$ = 25 °C; <u>Fig. 16</u>	-	0.78	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_{S}$ = 15 A; dI <sub>S</sub> /dt = -100 A/µs; V <sub>GS</sub> = 0 V;	-	20.3	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 20 V; T <sub>j</sub> = 25 °C	-	11.7	-	nC

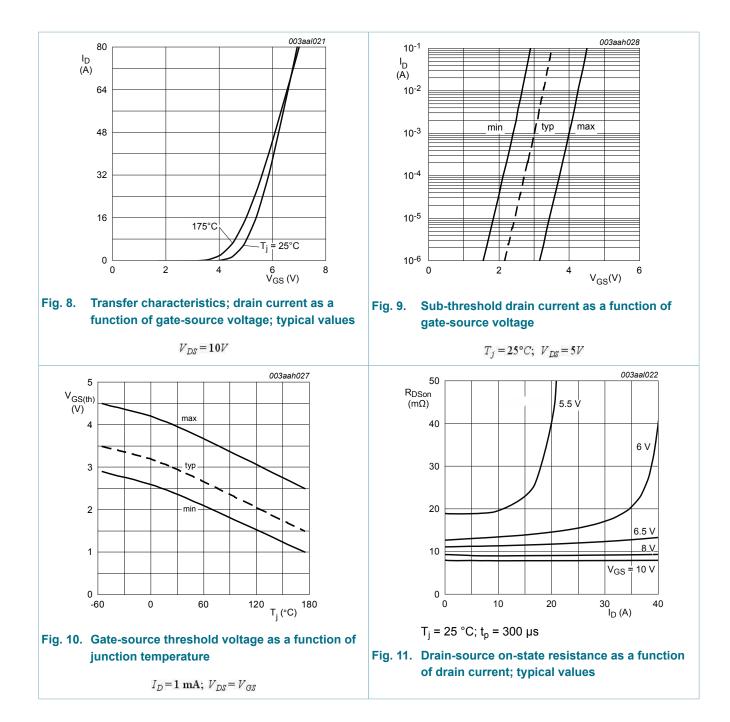


 $T_j = 25^{\circ}C; \ I_D = 15A$ 

ig. 7. Output characteristics; drain current as a function of drain-source voltage; typical values

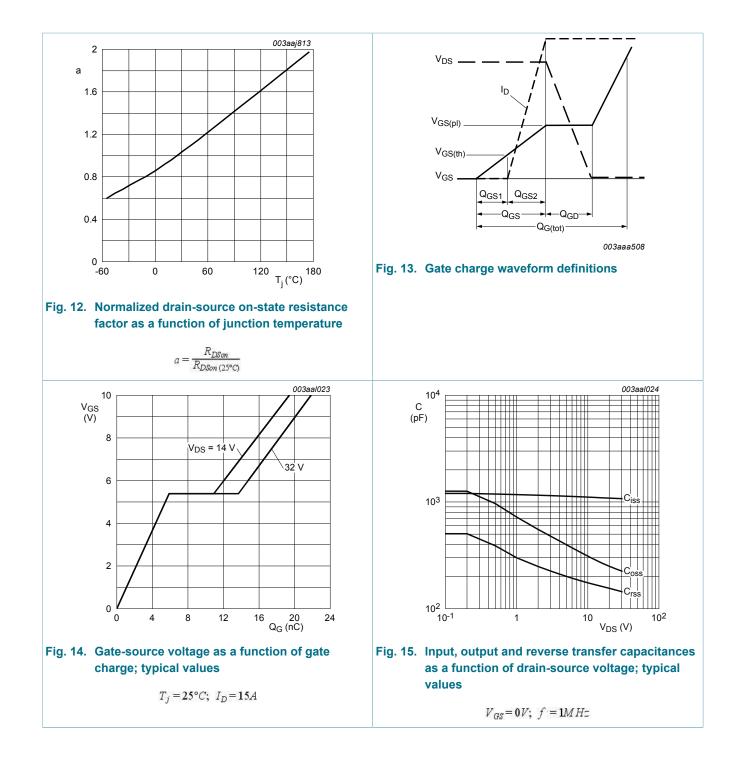
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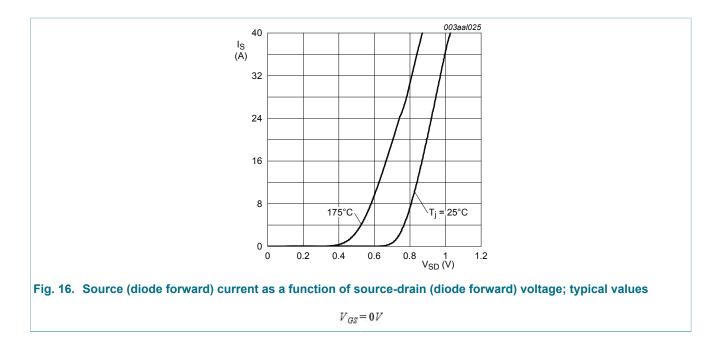
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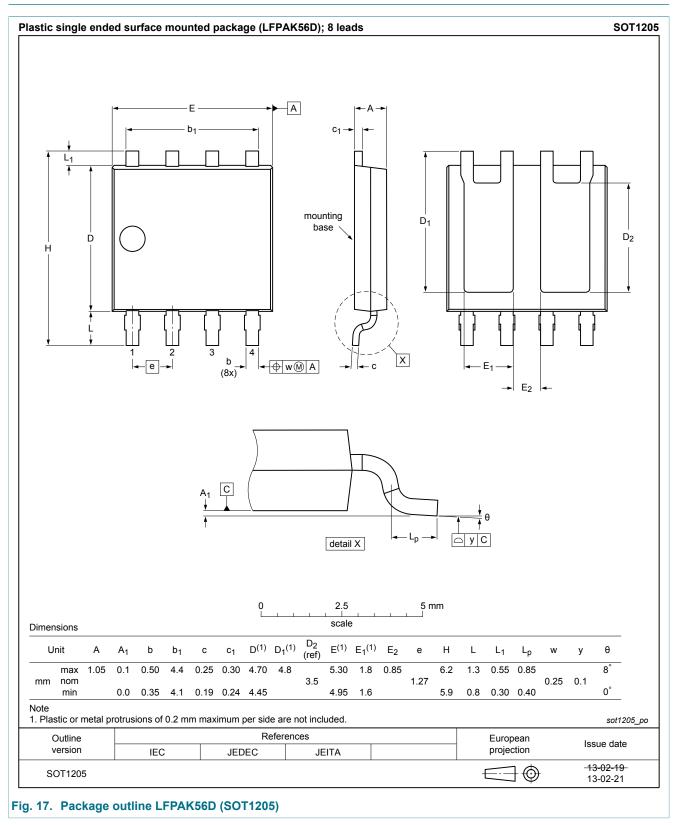
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### **11. Package outline**



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Product data sheet

#### Dual N-channel 40 V, 8.5 mΩ standard level MOSFET

### 12. Legal information

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Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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